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December 2013

# FDD18N20LZ

# N-Channel UniFET<sup>TM</sup> MOSFET 200 V, 16 A, 125 m $\Omega$

#### **Features**

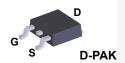
- R  $_{DS(on)}$  = 125 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V,  $I_{D}$  = 8 A
- Low Gate Charge (Typ. 30 nC)
- Low C<sub>RSS</sub> (Typ. 25 pF)
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- · ESD Improved Capability
- RoHS Compliant

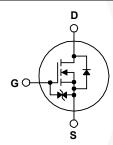
## **Applications**

- LED TV
- · Consumer Appliances
- · Uninterruptible Power Supply

# **Description**

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





# **MOSFET Maximum Ratings** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol		Parameter		FDD18N20LZ	Unit	
V <sub>DSS</sub>	Drain to Source Voltage			200	V	
$V_{GSS}$	Gate to Source Voltage			±20	V	
	Drain Current	- Continuous (T <sub>C</sub> = 25°C)		16	۸	
D	Drain Current	- Continuous (T <sub>C</sub> = 100°C)		9.6	A	
DM	Drain Current	- Pulsed			Α	
- AS	Single Pulsed Avalanche Energy (Note 2		(Note 2)	320	mJ	
AR	Avalanche Current		(Note 1)	16	Α	
- AR	Repetitive Avalanche Energy		(Note 1)	8.9	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	10	V/ns	
,	Davier Dissipation	$(T_C = 25^{\circ}C)$		89	W	
D	Power Dissipation	- Derate above 25°C		0.7	W/°C	
Γ <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.			300	°C	

#### **Thermal Characteristics**

Symbol	Parameter	FDD18N20LZ	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max.	1.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	83	- 6/00

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD18N20LZ	FDD18N20LZ	DPAK	Tape and Reel	330 mm	16 mm	2500 units

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	200	-	-	V
ΔBV <sub>DSS</sub> / Δ	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 μA, Referenced to 25°C	-	0.2	-	V/°C
TJ	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V	-	-	1	
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 160 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I <sub>GSS</sub>	Gate to Body Leakage Current	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±10	μΑ

#### On Characteristics

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	1.0	-	2.5	V
<b>D</b>	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 8A$	-	0.10	0.125	0
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 5 V, I <sub>D</sub> = 8 A	-	0.11	0.13	75
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = 20 \text{ V}, I_D = 2 \text{ A}$	-	11	-	S

## **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V		1185	1575	pF
C <sub>oss</sub>	Output Capacitance			190	255	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1011 12	-	25	40	pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10V		- \	30	40	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	$V_{DS} = 200 \text{ V I}_{D} = 16 \text{ A}$	-	3.5	-	nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge	V <sub>GS</sub> = 10 V (Not	e 4) -	8.5	-	nC

### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	15	40	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 100 \text{ V}, I_D = 16 \text{ A}$	-	20	50	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ = 10 V, $R_G$ = 25 $\Omega$	-	135	280	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	-	50	110	ns

#### **Drain-Source Diode Characteristics**

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current			-	16	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current			- 1	64	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 4 A	-	- /	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 4 A	-	105	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	0.4	-	μС

- 1: Repetitive rating: pulse-width limited by maximum junction temperature. 2: L = 2.5 mH,  $I_{AS}$  = 16 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C.
- 3:  $I_{SD} \le 16 \text{ A}$ , di/dt  $\le 200 \text{ A/}\mu\text{s}$ ,  $V_{DD} \le BV_{DSS}$ , starting  $T_J = 25^{\circ}\text{C}$ .
- 4: Essentially independent of operating temperature typical characteristics.

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

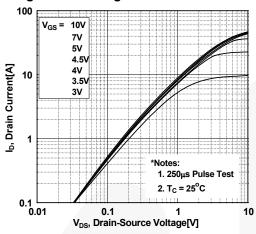


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

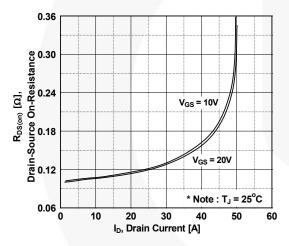
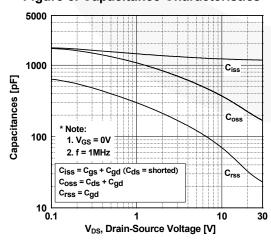


Figure 5. Capacitance Characteristics



**Figure 2. Transfer Characteristics** 

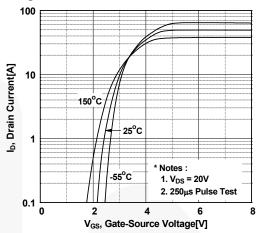
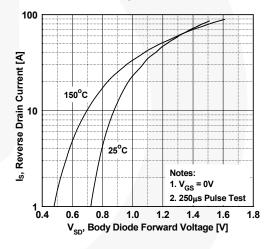
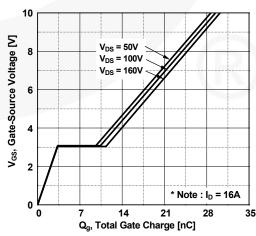


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



**Figure 6. Gate Charge Characteristics** 



# **Typical Performance Characteristics** (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

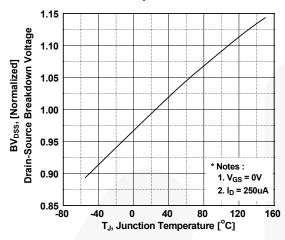


Figure 9. Maximum Safe Operating Area

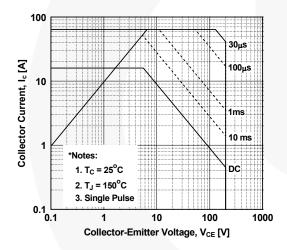


Figure 8. On-Resistance Variation vs. Temperature

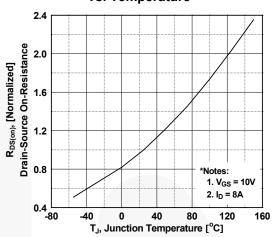


Figure 10. Maximum Drain Current vs. Case Temperature

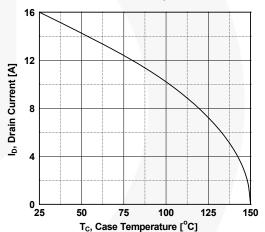
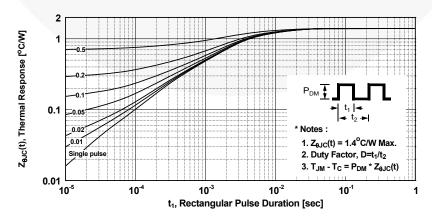


Figure 11. Transient Thermal Response Curve



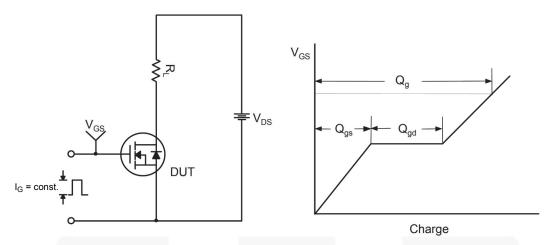


Figure 12. Gate Charge Test Circuit & Waveform

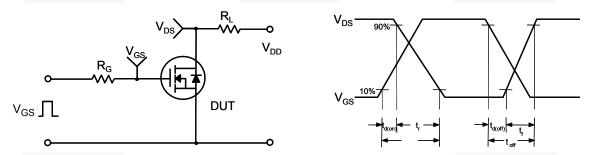


Figure 13. Resistive Switching Test Circuit & Waveforms

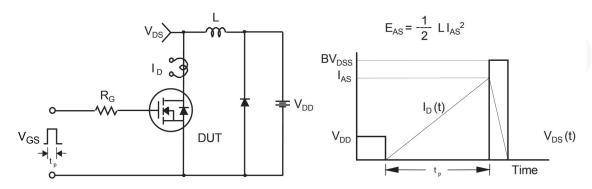
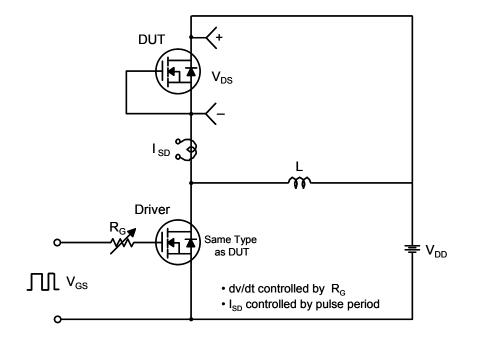


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



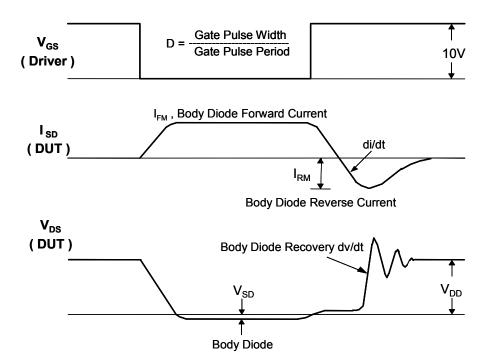


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

### **Mechanical Dimensions**

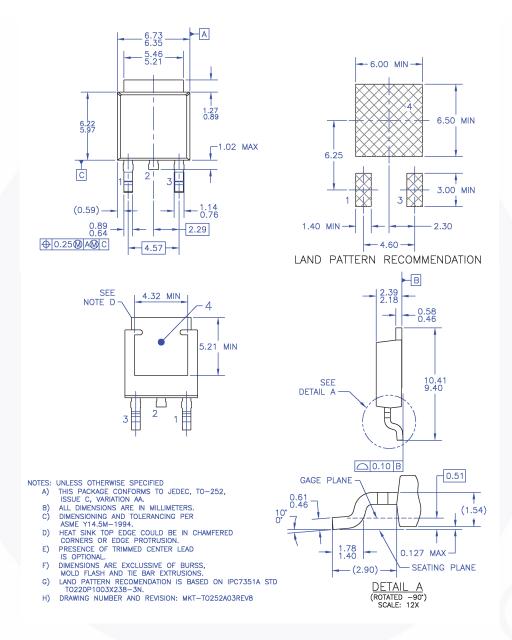


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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